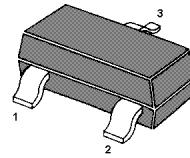


# MMBTSC3356

## NPN Silicon Epitaxial Planar Transistor

for microwave low noise amplifier at VHF, UHF and CATV band

The transistor is subdivided into three groups, Q, R and S, according to its DC current gain.



1. Base 2. Emitter 3. Collector  
TO-236 Plastic Package

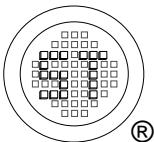
### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Collector Base Voltage	$V_{\text{CBO}}$	20	V
Collector Emitter Voltage	$V_{\text{CEO}}$	12	V
Emitter Base Voltage	$V_{\text{EBO}}$	3	V
Collector Current	$I_C$	100	mA
Power Dissipation	$P_{\text{tot}}$	200	mW
Junction Temperature	$T_j$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{\text{stg}}$	- 65 to + 150	$^\circ\text{C}$

### Characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{\text{CE}} = 10 \text{ V}$ , $I_C = 20 \text{ mA}$	$h_{\text{FE}}$	50	-	100	-
	$h_{\text{FE}}$	80	-	160	-
	$h_{\text{FE}}$	125	-	250	-
Collector Cutoff Current at $V_{\text{CB}} = 10 \text{ V}$	$I_{\text{CBO}}$	-	-	1	$\mu\text{A}$
Emitter Cutoff Current at $V_{\text{EB}} = 1 \text{ V}$	$I_{\text{EBO}}$	-	-	1	$\mu\text{A}$
Collector Base Breakdown Voltage at $I_C = 10 \mu\text{A}$	$V_{(\text{BR})\text{CBO}}$	20	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 1 \text{ mA}$	$V_{(\text{BR})\text{CEO}}$	12	-	-	V
Emitter Base Breakdown Voltage at $I_E = 10 \mu\text{A}$	$V_{(\text{BR})\text{EBO}}$	3	-	-	V
Collector Emitter Saturation Voltage at $I_C = 10 \text{ mA}$ , $I_B = 5 \text{ mA}$	$V_{\text{CE}(\text{sat})}$	-	-	0.5	V
Gain Bandwidth Product at $V_{\text{CE}} = 10 \text{ V}$ , $I_C = 20 \text{ mA}$	$f_T$	-	7	-	GHz
Feed-Back Capacitance at $V_{\text{CB}} = 10 \text{ V}$ , $f = 1 \text{ MHz}$	$C_{\text{re}}^1)$	-	-	1	pF

<sup>1)</sup> The emitter terminal and the case shall be connected to the guard terminal of the three-terminal capacitance bridge.



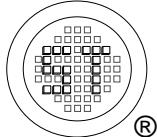
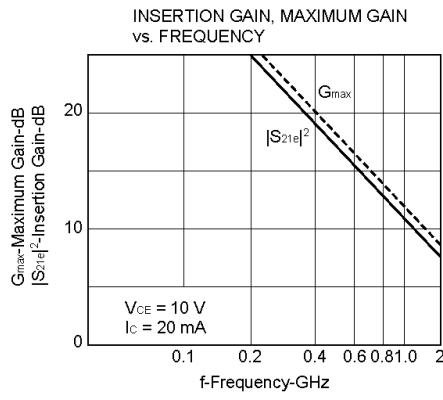
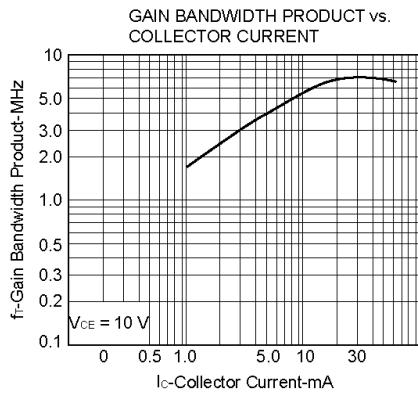
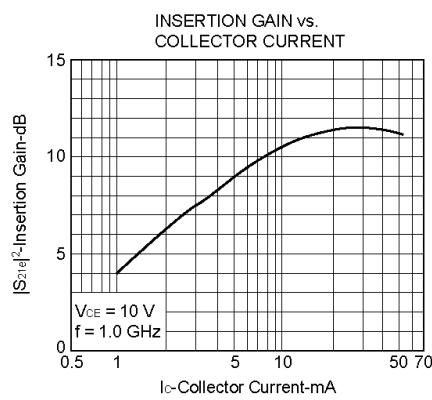
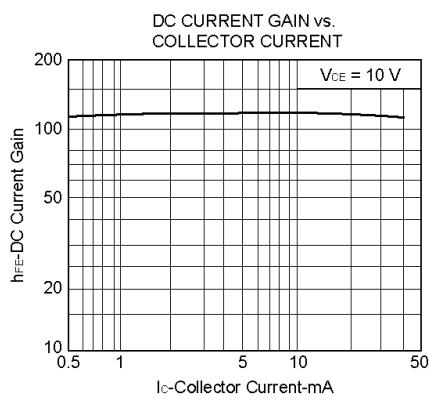
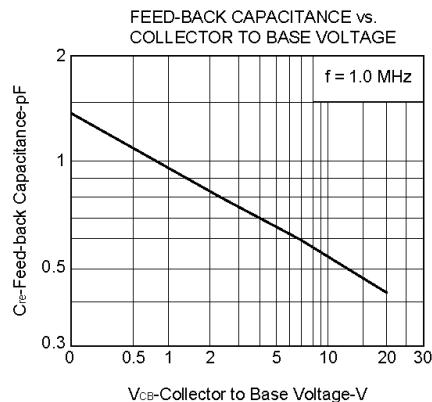
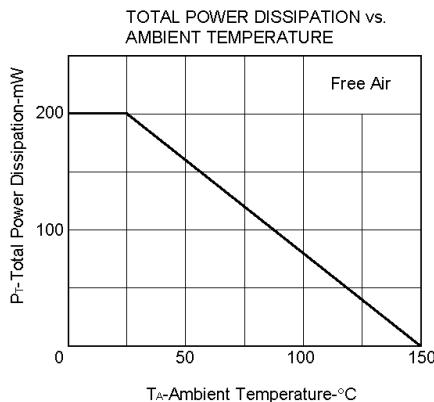
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ISO/TS 16949 : 2009 ISO 14001 : 2004 ISO 9001 : 2008 BS-OHSAS 18001 : 2007 IECQ QC 080000  
Certificate No. 160719000 Certificate No. 7116 Certificate No. 50713410 Certificate No. 7116 Certificate No. PRC-HSPM-14034

Dated: 16/03/2015 Rev: 01

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